



YOUSHANG SEMICONDUCTOR

设计研发新型功率器件

各类小信号开关

中低压及高压大电流等场效应管

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企业微信二维码



企业QQ二维码

Features

- $BV_{CEO} > 25V$
- $BV_{CBO} > 35V$ forward blocking voltage
- $I_C = 3A$ high Continuous Collector Current
- Low saturation voltage, $V_{CE(SAT)} < 120mV @ 1A$
- $R_{CE(SAT)} = 77m\Omega$ for a low equivalent On-Resistance
- 725mW Power dissipation
- h_{FE} specified up to 6A for high current gain hold up
- Complementary PNP Type: ZXTN749F

Mechanical Data

- Case: SOT23
- Case Material: molded plastic, "Green" molding compound
- UL Flammability Classification Rating 94V-0
- Moisture Sensitivity: Level 1 per J-STD-020
- Terminals: Finish – Matte Tin Plated Leads, Solderable per MIL-STD-202, Method 208
- Weight 0.008 grams (approximate)

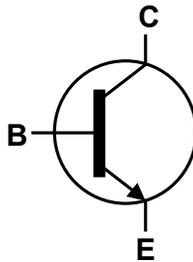
Applications

- MOSFET gate drivers
- Power switching in automotive and industrial applications
- Motor drive and control

SOT23



Top View



Device Symbol

Maximum Ratings (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

Characteristic	Symbol	Value	Unit
Collector-Base Voltage	V_{CB0}	35	V
Collector-Emitter Voltage	V_{CEO}	25	V
Emitter-Base Voltage	V_{EBO}	7	V
Continuous Collector Current	I_C	3	A
Peak Pulse Current	I_{CM}	6	A
Base Current	I_B	500	mA

Thermal Characteristics (@ $T_A = +25^{\circ}\text{C}$, unless otherwise specified.)

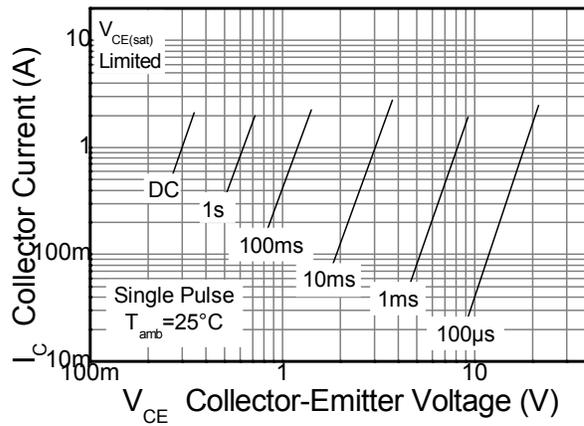
Characteristic	Symbol	Value	Unit
Power Dissipation (Note 5)	P_D	725	mW
Thermal Resistance, Junction to Ambient (Note 5)	$R_{\theta JA}$	172	$^{\circ}\text{C}/\text{W}$
Thermal Resistance, Junction to Leads (Note 6)	$R_{\theta JL}$	79	$^{\circ}\text{C}/\text{W}$
Operating and Storage Temperature Range	T_J, T_{STG}	-55 to +150	$^{\circ}\text{C}$

ESD Ratings (Note 7)

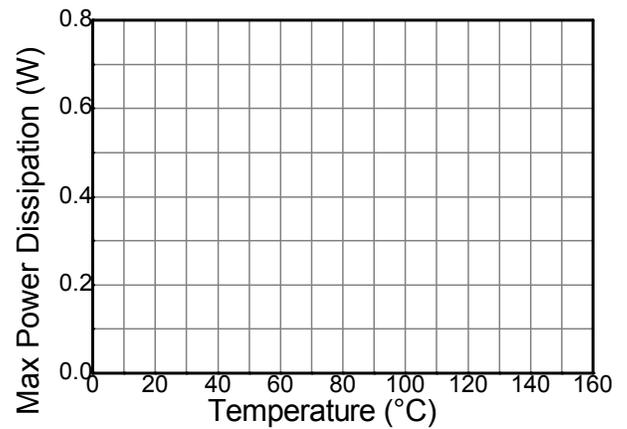
Characteristic	Symbol	Value	Unit	JEDEC Class
Electrostatic Discharge - Human Body Model	ESD HBM	$\geq 8,000$	V	3B
Electrostatic Discharge - Machine Model	ESD MM	≥ 400	V	C

- Notes:
5. For a device surface mounted on 15mm x 15mm x 1.6mm FR4 PCB with high coverage of single sided 1oz copper, in still air conditions; the device is measured when operating in a steady-state condition.
 6. Thermal resistance from junction to solder-point (at the end of collector lead).
 7. Refer to JEDEC specification JESD22-A114 and JESD22-A115.

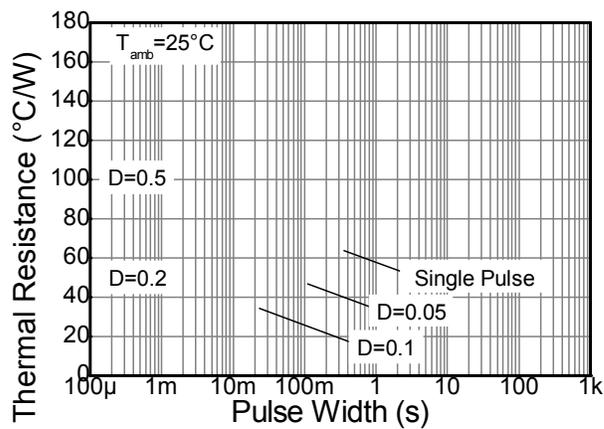
Thermal Characteristics and Derating information



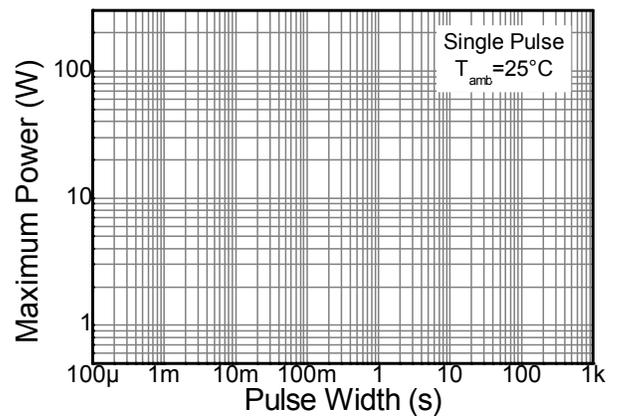
Safe Operating Area



Derating Curve



Transient Thermal Impedance



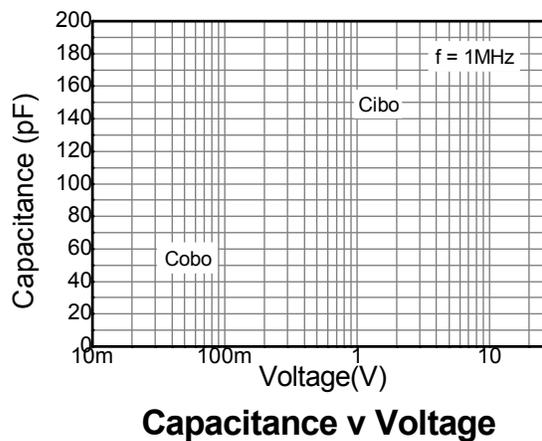
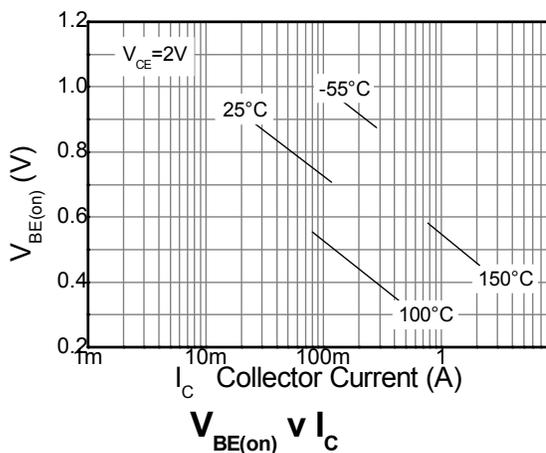
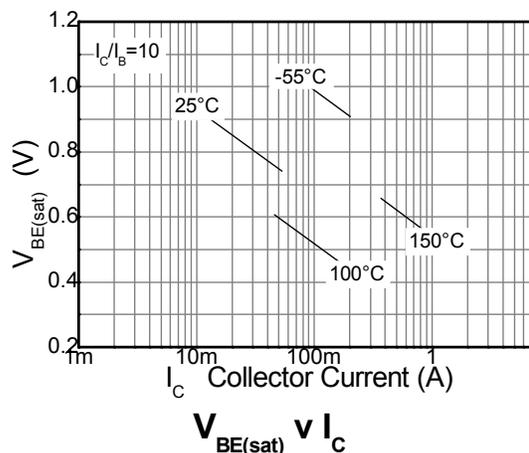
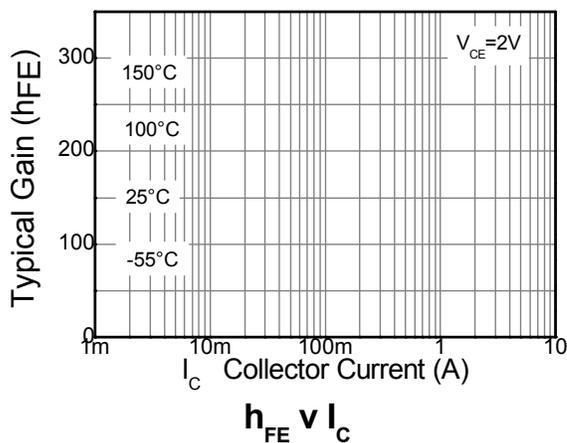
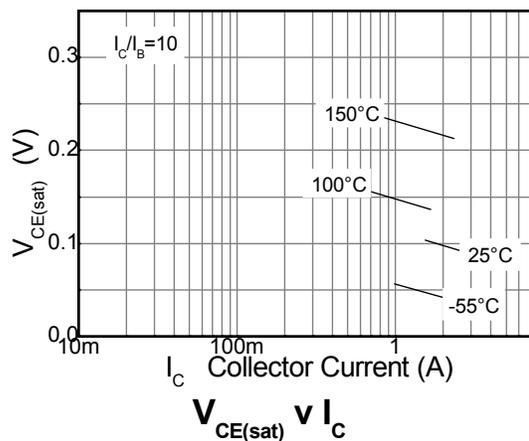
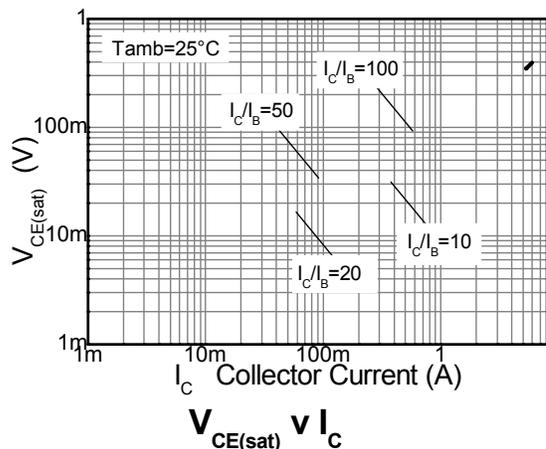
Pulse Power Dissipation

Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

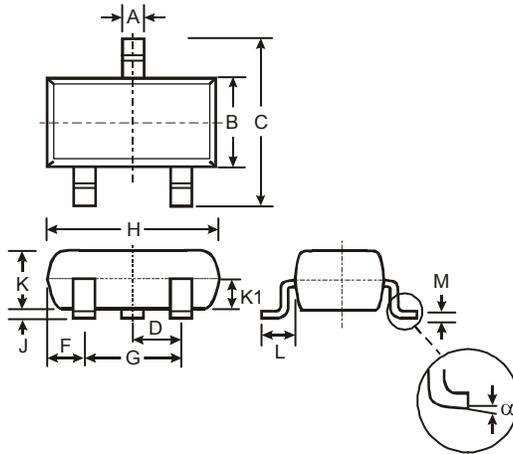
Characteristic	Symbol	Min	Typ	Max	Unit	Test Condition
Collector-Base Breakdown Voltage	BV_{CBO}	35	110	-	V	$I_C = 100\mu\text{A}$
Collector-Emitter Breakdown Voltage (Note 8)	BV_{CEO}	25	35	-	V	$I_C = 10\text{mA}$
Emitter-Base Breakdown Voltage	BV_{EBO}	7	8.1	-	V	$I_E = 100\mu\text{A}$
Collector Cut-off Current	I_{CBO}	-	<1	50 0.5	nA μA	$V_{CB} = 28\text{V}$ $V_{CB} = 28\text{V}, T_A = +100^\circ\text{C}$
Emitter Cut-off Current	I_{EBO}	-	<1	50	nA	$V_{EB} = 5.6\text{V}$
Static Forward Current Transfer Ratio (Note 8)	h_{FE}	200 175 155 50	320 280 250 85	500 - - -	-	$I_C = 100\text{mA}, V_{CE} = 2\text{V}$ $I_C = 1\text{A}, V_{CE} = 2\text{V}$ $I_C = 2\text{A}, V_{CE} = 2\text{V}$ $I_C = 6\text{A}, V_{CE} = 2\text{V}$
Collector-Emitter Saturation Voltage (Note 8)	$V_{CE(sat)}$	- -	70 200	120 300	mV	$I_C = 1\text{A}, I_B = 100\text{mA}$ $I_C = 3\text{A}, I_B = 300\text{mA}$
Base-Emitter Saturation Voltage (Note 8)	$V_{BE(sat)}$	-	900	1000	mV	$I_C = 1\text{A}, I_B = 100\text{mA}$
Base-Emitter Saturation Voltage (Note 8)	$V_{BE(on)}$	-	780	850	mV	$I_C = 1\text{A}, V_{CE} = 2\text{V}$

 Notes: 8. Measured under pulsed conditions. Pulse width $\leq 300\mu\text{s}$. Duty cycle $\leq 2\%$

Typical Electrical Characteristics (@ $T_A = +25^\circ\text{C}$, unless otherwise specified.)

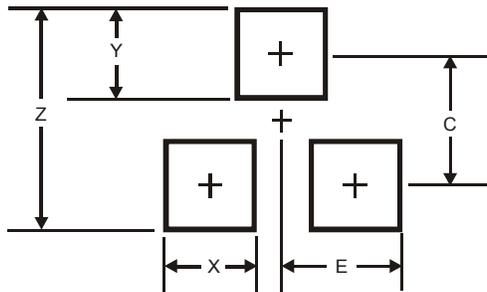


Package Outline Dimensions



SOT23			
Dim	Min	Max	Typ
A	0.37	0.51	0.40
B	1.20	1.40	1.30
C	2.30	2.50	2.40
D	0.89	1.03	0.915
F	0.45	0.60	0.535
G	1.78	2.05	1.83
H	2.80	3.00	2.90
J	0.013	0.10	0.05
K	0.903	1.10	1.00
K1	-	-	0.400
L	0.45	0.61	0.55
M	0.085	0.18	0.11
α	0°	8°	-
All Dimensions in mm			

Suggested Pad Layout



Dimensions	Value (in mm)
Z	2.9
X	0.8
Y	0.9
C	2.0
E	1.35